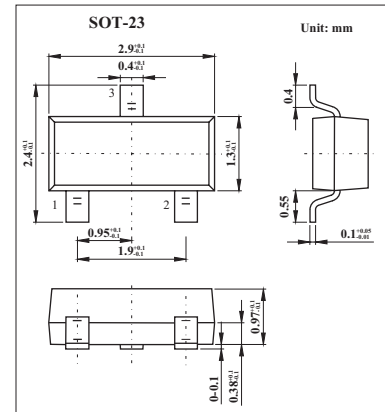


Silicon Schottky Diodes

BAT64 series



■ Features

- For low-loss, fast-recovery, meter protection bias isolation and clamping applications
- Integrated diffused guard ring
- Low forward current

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max	Unit
Diode reverse voltage	V_R	40	V
Forward current	I_F	250	mA
Average forward current (50/60Hz, sinus)	I_{FAV}	120	mA
Surge forward current ($t \leq 10$ ms)	I_{FSM}	800	mA
Total power dissipation $T_s = 61^\circ\text{C}$	P_{tot}	250	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Junction ambient (Note 1)	$R_{th JA}$	≤ 495	KW
Junction soldering point	$R_{th JS}$	≤ 355	KW

Note

1. Package mounted on epoxy pcb 40mm × 40 mm × 1.5 mm / 0.5cm² Cu

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I_R	$V_R = 25$ V, $T_a = 25^\circ\text{C}$			2	μA
		$V_R = 25$ V, $T_a = 85^\circ\text{C}$			200	
Forward voltage	V_F	$I_F = 1$ mA		320	350	mV
		$I_F = 10$ mA		385	430	V
		$I_F = 30$ mA		440	520	V
		$I_F = 100$ mA		570	750	V
Diode capacitance	C_T	$V_R = 1$ V, $f = 1$ MHz		4	6	pF

■ Marking

Type	BAT64	BAT64-04	BAT64-05	BAT64-06
Marking	63s	64s	65s	66s